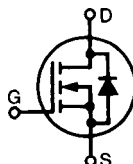


MegaMOS™ FET

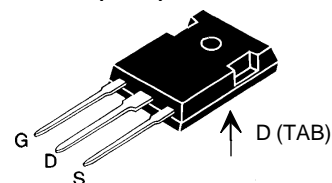
| | V_{DSS} | I_{D25} | $R_{DS(on)}$ |
|-------------------|-----------|-----------|---------------|
| IXTH / IXTM 11N80 | 800 V | 11 A | 0.95 Ω |
| IXTH / IXTM 13N80 | 800 V | 13 A | 0.80 Ω |

N-Channel Enhancement Mode



| Symbol | Test Conditions | Maximum Ratings | |
|---|---|-----------------------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 800 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$ | 800 | V |
| V_{GS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 11N80 | 11 A |
| | | 13N80 | 13 A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 11N80 | 44 A |
| | | 13N80 | 52 A |
| P_D | $T_C = 25^\circ\text{C}$ | 300 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| M_d | Mounting torque | 1.13/10 | Nm/lb.in. |
| Weight | | TO-204 = 18 g, TO-247 = 6 g | |
| Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s | | 300 | $^\circ\text{C}$ |

TO-247 AD (IXTH)



TO-204 AA (IXTM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
 - easy to drive and to protect
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|--|---|------|---------------------|
| | | min. | typ. | max. |
| V_{DSS} | $V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$ | 800 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 2 | | 4.5 V |
| I_{GSS} | $V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 100\text{ nA}$ |
| I_{DSS} | $V_{DS} = 0.8 \cdot V_{DSS}$ | | | 250 μA |
| | $V_{GS} = 0\text{ V}$ | | | 1 mA |
| $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ }I_{D25}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$, | 11N80 | | 0.95 Ω |
| | | 13N80 | | 0.80 Ω |

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|---|---|------|--------|
| | | min. | typ. | max. |
| g_{fs} | $V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test | 8 | 14 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 4500 | pF |
| C_{oss} | | | 310 | pF |
| C_{rss} | | | 65 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$, (External) | | 20 | 50 ns |
| t_r | | | 33 | 50 ns |
| $t_{d(off)}$ | | | 63 | 100 ns |
| t_f | | | 32 | 50 ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ | | 145 | 170 nC |
| Q_{gs} | | | 30 | 45 nC |
| Q_{gd} | | | 55 | 80 nC |
| R_{thJC} | | | 0.42 | K/W |
| R_{thCK} | | | 0.25 | K/W |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|---|---|------|--------------|
| | | min. | typ. | max. |
| I_S | $V_{GS} = 0\text{ V}$ | 11N80 13N80 | | 11 A 13 A |
| I_{SM} | Repetitive; pulse width limited by T_{JM} | 11N80 13N80 | | 44 A 52 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$ | | | 1.5 V |
| t_{rr} | $I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ | | 800 | ns |

TO-247 AD (IXTH) Outline

Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ∅P | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 | BSC | 242 | BSC |

TO-204AA (IXTM) Outline

Pins: 1 - Gate 2 - Source
Case - Drain

| Dim. | Millimeter | | Inches | |
|-----------------|------------|-------|--------|------|
| | Min. | Max. | Min. | Max. |
| A | 6.4 | 11.4 | .250 | .450 |
| A ₁ | | 3.42 | | .135 |
| ∅b | .97 | 1.09 | .038 | .043 |
| ∅D | | 22.22 | | .875 |
| e | 10.67 | 11.17 | .420 | .440 |
| e ₁ | 5.21 | 5.71 | .205 | .225 |
| L | 7.93 | | .312 | |
| ∅p | 3.84 | 4.19 | .151 | .165 |
| ∅p ₁ | 3.84 | 4.19 | .151 | .165 |
| q | 30.15 | BSC | 1.187 | BSC |
| R | | 13.33 | | .525 |
| R ₁ | | 4.77 | | .188 |
| s | 16.64 | 17.14 | .655 | .675 |

Fig. 1 Output Characteristics

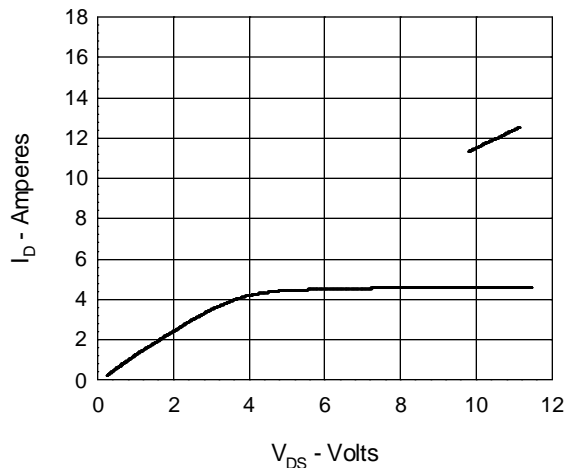


Fig. 2 Input Admittance

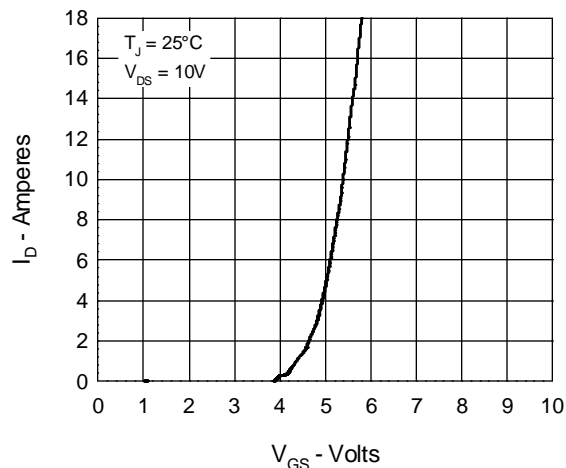


Fig. 3 $R_{DS(on)}$ vs. Drain Current

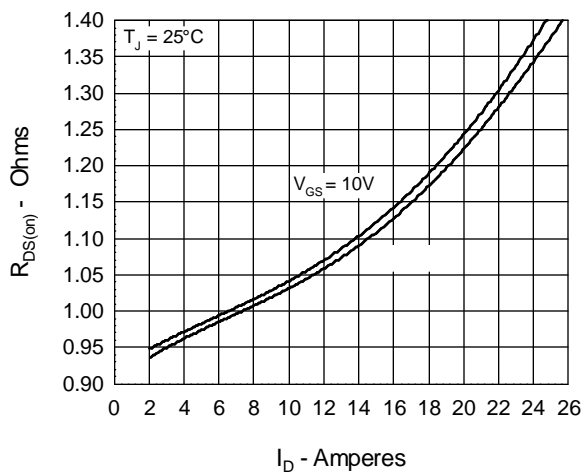


Fig. 4 Temperature Dependence of Drain to Source Resistance

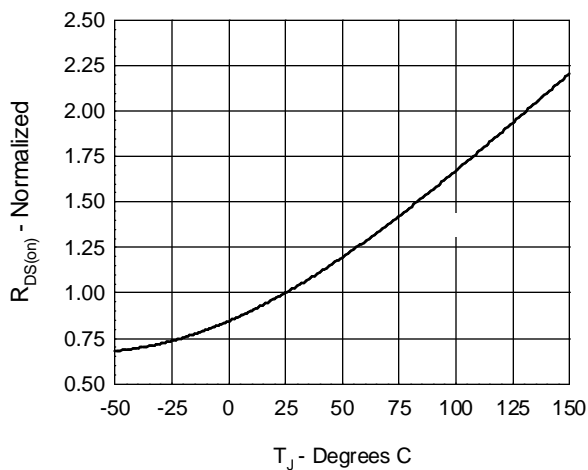


Fig. 5 Drain Current vs. Case Temperature

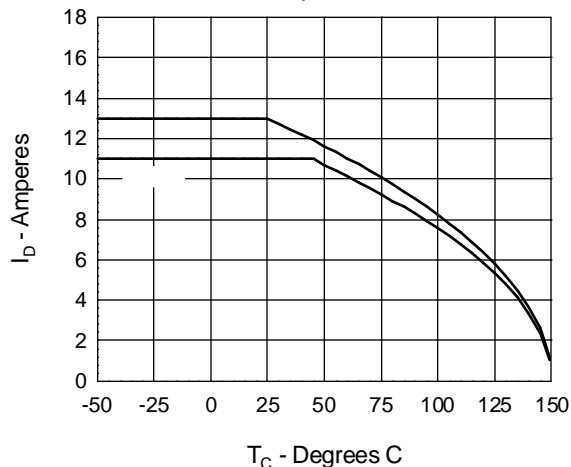
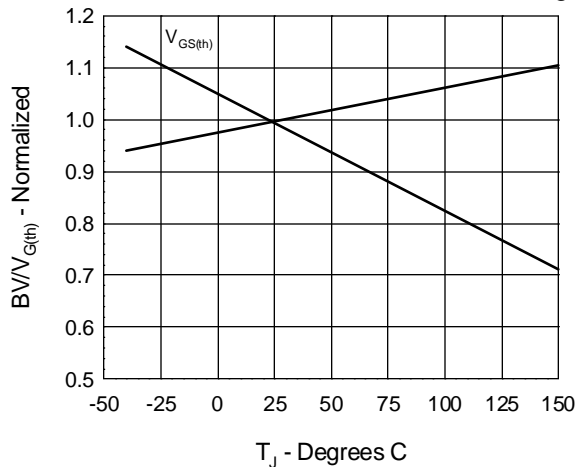


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage



IXYS reserves the right to change limits, test conditions, and dimensions.

Fig.7 Gate Charge Characteristic Curve

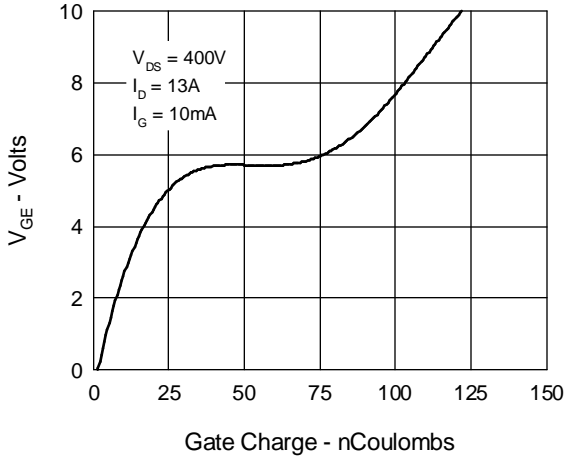


Fig.8 Forward Bias Safe Operating Area

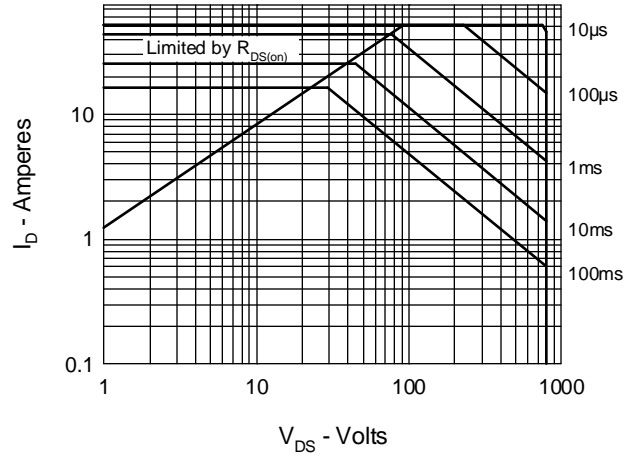


Fig.9 Capacitance Curves

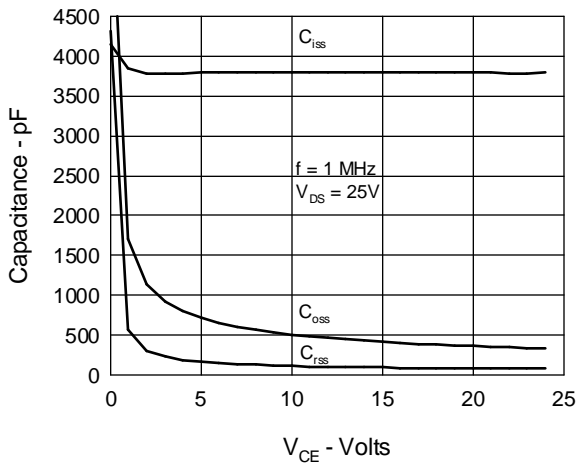


Fig.10 Source Current vs. Source to Drain Voltage

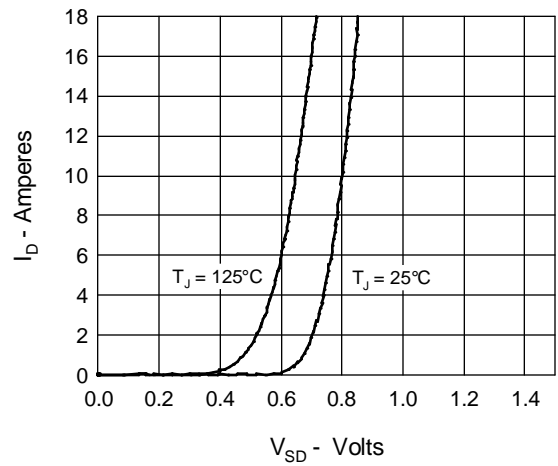


Fig.11 Transient Thermal Impedance

